SHANGHAI SUNRISE ELECTRONICS CO., LTD.

1N4001G THRU 1N4007G

GLASS PASSIVATED
JUNCTION RECTIFIER

TECHNICAL SPECIFICATION

VOLTAGE: 50 TO 1000V CURRENT: 1.0A

FEATURES

- Molded case feature for auto insertion
- Glass passivated chip
- High current capability
- Low leakage current
- High surge capability
- High temperature soldering guaranteed: 250^{o}C/10sec/0.375"(9.5mm) lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode
- Mounting position: Any

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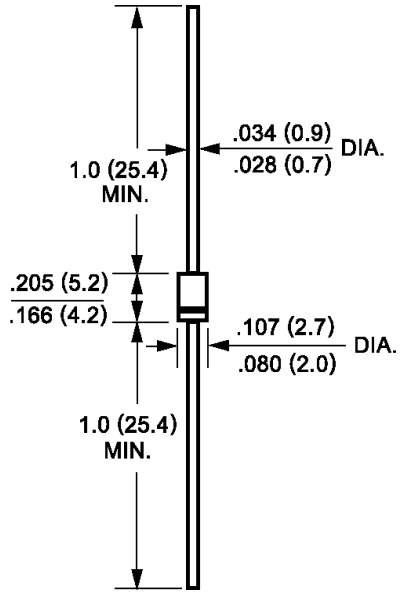

Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25^{o}C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	1N4001G	1N4002G	1N4003G	1N4004G	1N4005G	1N4006G	1N4007G	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current (9.5mm lead length, at T_a=75^{o}C)	$I_{F(AV)}$	1.0							A
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I_{FSM}	30.0							A
Maximum Instantaneous Forward Voltage (at rated forward current)	V_F	1.1							V
Maximum DC Reverse Current T_a=25^{o}C	I_R	5.0							μA
(at rated DC blocking voltage) T_a=100^{o}C		50							μA
Typical Junction Capacitance (Note 1)	C_J	15.0							pF
Typical Thermal Resistance (Note 2)	R_{θ}(ja)	50.0							^{o}C/W
Storage and Operation Junction Temperature	T_{STG},T_J	-65 to +150							^{o}C

Note:
1.Measured at 1.0 MHz and applied voltage of 4.0V_{dc}
2.Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C. board mounted